

## **Patents and Disclosures (9)**

### **1. Optical Microprobe with Subwavelength Resolution**

V. N. Astratov, Provisional Application for US Patent, 2008

### **2. Method of Determination of Energy Parameters of High-Resistivity Electrooptic Semiconductors**

V.N. Astratov, A.V. Ilinskii, and A.S. Furman

Patent No 1833054 (In Russia), 1992

### **3. Method of Measurements of Carriers Drift Mobility in High-Resistivity Semiconductors**

V.N. Astratov, A.S. Furman, and A.V. Ilinskii

Patent No 1604099 (in Russia), 1990

### **4. Method of Measurements of Electrical Parameters of High-Resistivity Semiconductors**

V.N. Astratov, A.V. Ilinskii, and M.B. Melnikov

Patent No 1487754 (in Russia), 1989

### **5. Method of Measurements of Population of Trapping Levels in High-Resistivity Semiconductors**

V.N. Astratov, A.V. Ilinskii, and M.B. Melnikov

Patent No 1468327 (in Russia), 1988

### **6. Method of Conductivity Measurements in High-Resistivity Semiconductors**

V.N. Astratov, A.V. Ilinskii, M.B. Melnikov, S.N. Reznikov, and I.N. Hootorskoy

Patent No 1400391 (in Russia), 1988

### **7. Method of Measurements of Quantum Yield of Photo-Effect in High-Resistivity Semiconductors**

V.N. Astratov, A.V. Ilinskii, and M.B. Melnikov

Patent No 1289322 (in Russia), 1986

### **8. Method of Determination of Energy of Trapping Levels in High-Resistivity Crystals**

V.N. Astratov, A.V. Ilinskii, M.B. Melnikov, O.M. Rusakov, S.N. Reznikov, and L.N. Linnik

Patent No 1235408 (in Russia), 1986

### **9. Method of Determination of Distribution of Electric Field by Transverse Electrooptic Effect in Crystals**

V.N. Astratov, A.V. Ilinskii, L.N. Linnik, and S.N. Reznikov

Patent No 1045728 (in Russia), 1983